



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89 Plastic-Encapsulate Transistors

BC869 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 500 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -2 A

Collector-base voltage

$V_{(BR)CBO}$: -32 V

Operating and storage junction temperature range

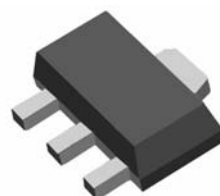
T_J, T_{stg} : $-65^{\circ}C$ to $+150^{\circ}C$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-0.1mA, I_E=0$	-32		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-20		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-0.1mA, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-25V, I_E=0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-10V, I_C=-5mA$ $V_{CE}=-1V, I_C=-500mA$ $V_{CE}=-1V, I_C=-1A$	50 100 60	375	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-500mA$	100 160	250 375	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-1A, I_B=-100mA$		0.5	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-10mA$ $f=100MHz$	40		MHz

DEVICE MARKING

BC869=CEC BC869-16=CGC BC869-25=CHC